



2:1 MIPI 4-Data Lane Switch

#### **Features**

- SPDT (10x) Switch Type and Signal Type Support D-PHY and C-PHY
- Data Rate: D-PHY (2.5Gbps) 4-Data Lane and C-PHY (2.5Gsps)
   3-Data Lane
- Supports 2:1 clock differential signal
- -3 dB Bandwidth: 4.1 GHz Typical
- Low Crosstalk: -30 dB@1.25 GHz
- Input Signals 0 to 1.3V
- RON: 6Ω Typical LP & HS MIPI
- $\Delta R_{ON}$ : 0.1 $\Omega$  Typical LP & HS MIPI
- R<sub>ON</sub>\_FLAT: 0.3Ω Typical LP & HS MIPI
- I<sub>CCZ</sub>: 0.5uA Typical
- I<sub>CC</sub>: 32μA Max
- C<sub>ON</sub>: 1.5pF Typical
- Skew of Opposite Transitions of the Same Output: 6ps Typical
- V<sub>DD</sub> Operating Range: 1.5V to 3.6V
- ESD Tolerance: 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
  - https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
  - 36-Ball, WLCSP (GH) 2.10x2.10

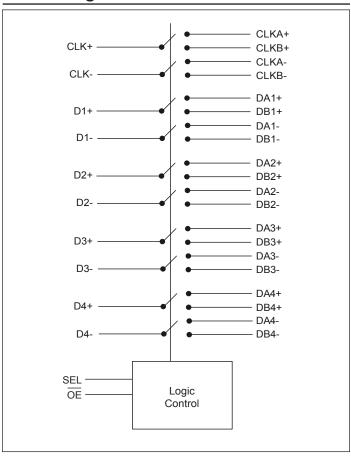
### Application(s)

- Cellular Phones, Smart Phone
- Tablets
- Laptops
- Displays

### Description

The DIODES™ PI3WVR2646 is a four-data-lane MIPI-D-PHY switch. This 10 channel single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR2646 is designed for the MIPI specification and allows connection to a CSI or DSI module.

## **Block Diagram**



#### Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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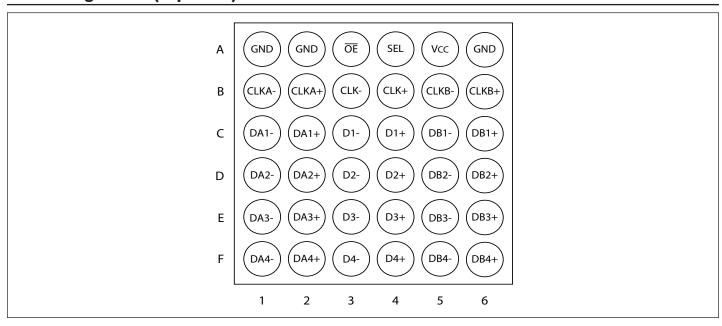




### **Truth Table**

SEL	ŌE	Function
LOW	LOW	CLK+ = CLKA+, CLK- = CLKA-, Dn(+/-) = DAn(+/-)
HIGH	LOW	CLK+ = CLKB+, CLK- = CLKB-, Dn(+/-) = DBn(+/-)
X	HIGH	Clock and Data Ports High Impedance

# Pin Configuration(Top View)



# **Pin Description**

Pin#	Pin Name	Type	Description
A1	GND	Ground	Ground
A2	GND	Ground	Ground
A3	ŌE	I	Output enable. if $\overline{OE}$ is low, IC is enabled. if $\overline{OE}$ is high, IC is power down and all I/Os are Hi-Z
A4	SEL	I	Switch logic control
A5	VCC	Power	1.5V to 3.6V power supply
A6	GND	Ground	Ground
B1	CLKA-	I/O	Clock negative differential signal for port A
B2	CLKA+	I/O	Clock positive differential signal for port A
В3	CLK-	I/O	Clock negative differential signal for COM port
B4	CLK+	I/O	Clock positive differential signal for COM port
B5	CLKB-	I/O	Clock negative differential signal for port B
В6	CLKB+	I/O	Clock positive differential signal for port B
C1	DA1-	I/O	Negative differential signal 1 for port A
C2	DA1+	I/O	Positive differential signal 1 for port A





# Pin Description Cont.

Pin#	Pin Name	Type	Description	
С3	D1-	I/O	Negative differential signal 1 for COM port	
C4	D1+	I/O	Positive differential signal 1 for COM port	
C5	DB1-	I/O	Negative differential signal 1 for port B	
C6	DB1+	I/O	Positive differential signal 1 for port B	
D1	DA2-	I/O	Negative differential signal 2 for port A	
D2	DA2+	I/O	Positive differential signal 2 for port A	
D3	D2-	I/O	Negative differential signal 2 for COM port	
D4	D2+	I/O	Positive differential signal 2 for COM port	
D5	DB2-	I/O	Negative differential signal 2 for port B	
D6	DB2+	I/O	Positive differential signal 2 for port B	
E1	DA3-	I/O	Negative differential signal 3 for port A	
E2	DA3+	I/O	Positive differential signal 3 for port A	
E3	D3-	I/O	Negative differential signal 3 for COM port	
E4	D3+	I/O	Positive differential signal 3 for COM port	
E5	DB3-	I/O	Negative differential signal 3 for port B	
E6	DB3+	I/O	Positive differential signal 3 for port B	
F1	DA4-	I/O	Negative differential signal 4 for port A	
F2	DA4+	I/O	Positive differential signal 4 for port A	
F3	D4-	I/O	Negative differential signal 4 for COM port	
F4	D4+	I/O	Positive differential signal 4 for COM port	
F5	DB4-	I/O	Negative differential signal 4 for port B	
F6	DB4+	I/O	Positive differential signal 4 for port B	





## **Absolute Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)

$V_{CC}$ , Supply Voltage,0.5V to 4.5V
$V_{CNTRL},$ DC Input Voltage $(\overline{OE}, SEL)^{(1)}0.5V$ to $V_{CC}$
V <sub>SW</sub> , DC Switch I/O Voltage <sup>(1,2)</sup> 0.3V to 2.5V
I <sub>IK</sub> , DC Input Diodes Current50mA
I <sub>OUT</sub> , DC Output Current25mA
$T_{STG}$ , Storage Temperature65°C to +150°C
Tj, Junction Temperature
ESD:
Human Body Model, JEDEC: JESD22-A114, All Pins2.0kV
Charged Device Model IEDEC: IESD22-C101 1 0kV

#### Note:

Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### Note:

- 1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
- 2. V<sub>SW</sub> refers to analog data switch paths.

## **Recommended Operating Conditions**

The Recommended operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

Symbol	Description	<b>Test Conditions</b>	Min.	Max.	Units
$V_{CC}$	Supply Voltage		1.5	3.6	V
V <sub>CNTRL</sub>	Control Input Voltage (SEL, $\overline{OE}$ ) <sup>(1)</sup>		0	V <sub>CC</sub>	V
V <sub>SW</sub>	Switch I/O Voltage (CLV D. CLVA CLVD DA DD.)	- HS Mode	0	0.5	V
	Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-)	- LP Mode	0	1.3	V
T <sub>A</sub>	Operating Temperature		-40	+85	°C

#### Note:

#### **DC** and Transient Characteristics

All typical values are at  $T_A = 25$ °C unless otherwise specified.

Cbl	Danielin	T4 C 1'4'	N/ (N/)	$T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$			TI*4
Symbol	Description	Test Conditions	V <sub>CC</sub> (V)	Min.	Тур.	Max.	Units
$V_{IK}$	Clamp Diode Voltage (OE, SEL)	$I_{IN} = -18mA$	1.5	-1.2		-0.6	V
$V_{IH}$	Input Voltage High	SEL, OE	1.5 to 3.3	1.0			V
$V_{\rm IL}$	Input Voltage Low	SEL, OE	1.5 to 3.3			0.5	V
I <sub>IN</sub>	Control Input Leakage (OE, SEL)	$V_{CNTRL} = 0$ to $V_{CC}$	3.3	-0.5		0.5	μΑ
I <sub>NO(OFF)</sub> I <sub>NC(OFF)</sub>	Off Leakage Current of Port	$V_{SW} = 0.0 \le DATA \le 1.3V$	3.3	-0.5		0.5	μΑ
I <sub>A(ON)</sub>	On Leakage Current of Common Ports	$V_{SW} = 0.0 \le DATA \le 1.3V$	3.3	-0.5		0.5	μА

<sup>1.</sup> The control inputs must be held HIGH or LOW; they must not float.





### DC and Transient Characteristics Cont.

G 1.1	Description	T (C P)	TI (TI)	$T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$			TT •4
Symbol		<b>Test Conditions</b>	V <sub>CC</sub> (V)	Min.	Тур.	Max.	Units
I <sub>OFF</sub>	Power-Off Leakage Current (All I/O Ports)	$V_{SW} = 0.0 \text{ or } 1.3 \text{V}$	0	-0.5		0.5	μА
$I_{OZ}$	Off-State Leakage	$\frac{V_{SW} = 0.0 \le DATA \le 1.3V,}{OE = High}$	3.6	-0.5		0.5	μА
		$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5				
R <sub>ON_MIPI_HS</sub>	Switch On Resistance for HS MIPI	SEL = V <sub>CC</sub> or 0V, All I/O	2.5		6		Ω
		Switches = 0.2V	3.3				
		$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5				
R <sub>ON_MIPI_LP</sub>	Switch On Resistance for LP MIPI	SEL = V <sub>CC</sub> or 0V, All I/O Switches = 1.2V	2.5		6		Ω
			3.3				
	On Resistance Matching Between HS MIPI Channels <sup>(1)</sup>	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ , $SEL = V_{CC}$ or $0V$ , $All\ I/O$ Switches = 0.2V	1.5		0.1		
$\Delta R_{ON\_MIPI\_HS}$			2.5				Ω
			3.3				
	On Resistance Matching Between LP MIPI Channels <sup>(1)</sup>	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ , $SEL = V_{CC}$ or $0V$ , $All\ I/O$ Switches = 1.2V	1.5		0.1		
$\Delta R_{ON\_MIPI\_LP}$			2.5				Ω
		owitches = 1.2 v	3.3				
R <sub>ON_FLAT_</sub>	On Resistance Flatness for HS MIPI	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ , $SEL = V_{CC}$ or $0V$ , $All\ I/O$ Switches = 0 to $0.5V$	1.5		0.2		
MIPI_HS			2.5		0.3		Ω
			3.3				
R <sub>ON_FLAT_</sub>	On Projection of Flattering for LD MIDI	$I_{ON} = -8 \text{mA}, \overline{OE} = 0 \text{V},$ $SEL = V_{CC} \text{ or } 0 \text{V}, \text{ All I/O}$ Switches = 0  to  1.3 V	1.5		0.2		
MIPI_LP	On Resistance Flatness for LP MIPI		3.3		0.3		Ω
			3.3				
$I_{CC}$	Quiescent Supply Current	$V_{SEL} = 0$ or $V_{CC}$ , $I_{OUT} = 0$ , $OE = 0V$	3.6		15	32	μΑ
$I_{CCZ}$	Quiescent Supply Current (High Impedance)	$\label{eq:VSEL} \begin{array}{ c c c }\hline V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,\\ \hline OE = High \end{array}$	3.6		0.5	1.0	μА
$I_{CCT}$	$\label{eq:local_control} Increase in I_{CC} \ Current \ Per \ Control \\ Voltage \ and \ V_{CC}$	$V_{SEL} = 0$ or $V_{CC}$ , $\overline{OE} = 1.5V$	3.6		1		μА





### **AC Electrical Characteristics**

All typical values are for  $V_{CC}=3.3V$  and  $T_A=25^{\circ}C$  unless otherwise specified.

6 1 1	Description	T. (C. P.)	W ON	$T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$			TT *4
Symbol		<b>Test Conditions</b>	$V_{CC}(V)$	Min.	Тур.	Max.	Units
t <sub>INIT</sub>	Initialization Time $V_{CC}$ to $Output^{(1)}$	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		60		μs
t <sub>EN</sub>	Enable Time $\overline{\rm OE}$ to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		60	150	μs
t <sub>DIS</sub>	Disable Time OE to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		35	250	ns
t <sub>ON</sub>	Turn-On Time SEL to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		350	1500	ns
t <sub>OFF</sub>	Turn-Off Time SEL to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ $= 0.6V$	1.5 to 3.6		125	800	ns
$t_{BBM}$	Break-Before-Make Time	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6			1000	ns
$t_{PD}$	Propagation Delay <sup>(1)</sup>	$C_L = 0$ pF, $R_L = 50\Omega$	1.5 to 3.6			0.25	ns
O <sub>IRR</sub>	Differential Off Isolation for MIPI <sup>(1)</sup>	$\frac{R_L}{OE} = 50\Omega, f = 1250MHz,$ $\frac{R_L}{OE} = HIGH, V_{SW} = 0.5V$	1.5 to 3.6		-26		dB
$X_{TALK}$	Differential Crosstalk for MIPI <sup>(1)</sup>	$\begin{aligned} R_L &= 50\Omega, \ f = 1250 MHz, \\ SEL &= HIGH, \ V_{SW} = 0.5V \end{aligned}$	1.5 to 3.6			-30	dB
I <sub>LOSS</sub>	Differential Insertion Loss <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF,$ $f = 1250MHz, V_{SW} = 0.5V$	1.5 to 3.6		-0.8		
BW	Differential -3db Bandwidth <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.5V	1.5 to 3.6	3	4.1		GHz

#### Note:

<sup>1.</sup> Guaranteed by characterization.





# **High-Speed-Related AC Electrical Characteristics**

Carrab al	Description	Took Conditions	V <sub>CC</sub>	$T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$			
Symbol	Description	<b>Test Conditions</b>	(V)	Min.	Тур.	Max.	Units
	D-PHY HS Mode Skew of Opposite Transitions of the Same Output <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF, V_{SW} = 0.3V$	1.5 to 3.6		4		
t <sub>SK(P)</sub>	C-PHY HS Mode Skew of 3 channels in same lane	$R_L = 50\Omega, C_L = 0pF, V_{SW} = 0.5V$	1.5 to 3.6		4		ps
	D-PHY HS Mode Skew of all group A or group B channels <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF, V_{SW} = 0.3V$	1.5 to 3.6		8		

#### Note:

### Capacitance

Sb al	Decemination	Total Conditions	T <sub>A</sub> =			
Symbol	Description	Test Conditions	Min.	Тур.	Max.	Units
C <sub>IN</sub>	Control Pin Input Capacitance <sup>(1)</sup>	$V_{CC} = 0V$ , $f = 1MHz$		2.1		pF
C <sub>ON</sub>	On Capacitance <sup>(1)</sup>	$V_{CC} = 3.3V$ , $\overline{OE} = 0V$ , $f = 1250MHz$ (In HS common value)		1.5		pF
C <sub>OFF</sub>	Off Capacitance <sup>(1)</sup>	$V_{CC}$ or $\overline{OE}$ = 3.3V, f = 1250MHz (Both sides in HS common value)		0.9		pF

#### Note:

## **Part Marking**

PI3WVR 2646GHE ZYYWWXX

Z: Die Rev

YY: Date Code (Year) WW: Date Code (Workweek) 1st X: Assembly Site Code

2nd X: Fab Site Code

<sup>1.</sup> Guaranteed by characterization.

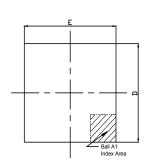
<sup>1.</sup> Guaranteed by characterization.

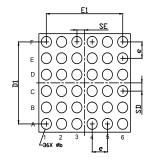




# **Packaging Mechanical**

### 36-WLCSP (GH)

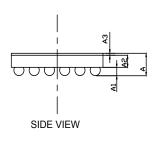


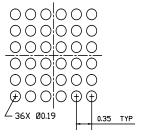


PKG. DIMENSIONS(MM) SYMBOL Min. Nom. Max. 0.393 0.438 0.483 A1 0.135 0.155 0.175 0.258 0.278 A2 0.238 A3 0.020 0.025 | 0.030 2.100 D 2.070 2.130 2.070 2.100 2.130 D1 1.700 | 1.750 | 1.800 1.700 1.750 E1 0.190 0.210 0.230 b 0.350BSC SD 0.175 BSC SE 0.175 BSC

**TOP VIEW** 







BOTTOMRECOMMEND LAND PATTERN VIEW

#### Note:

1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).

PERICON AND ENABLING SERIAL CONNECTIVITY

DATE: 02/10/20

REVISION:A

DESCRIPTION: 36-Ball, WLCSP, 2.10x2.10 (X1-WLB2121-36)

PACKAGE CODE: GH (GH36)

DOCUMENT CONTROL #: PD-2252

For latest package info.

20-1127

 $please\ check:\ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/packaging-mechanical-and-thermal-characteristics/packaging-mech$ 

# **Ordering Information**

Ordering Code	Package Code	Package Description
PI3WVR2646GHEX	GH	36-Ball, 2.10x2.10, (WLCSP) X1-WLB2121-36

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





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